

ABSTRACT

A hermetic sealing cap (1) capable of suppressing deterioration of the characteristics of an electronic component (20), reducing the material cost, using solder containing no Pb and suppressing lowering of airtightness is obtained. This hermetic sealing cap comprises a low thermal expansion layer (2), an Ni-Co alloy layer (3), formed on the surface of the low thermal expansion layer, mainly composed of Ni containing a diffusion accelerator, an Ni layer (4) formed on the surface of the Ni-Co alloy layer and a solder layer (5) mainly composed of Sn formed on a region of the surface of the Ni layer to which an electronic component storing member (10) is bonded. The Ni layer has a function of inhibiting the Ni-Co alloy layer from diffusing into the solder layer at about 235°C (first temperature) while diffusing the Ni-Co alloy layer into the solder layer through the Ni layer when the solder layer bonds to the electronic component storing member at about 300°C to about 320°C (second temperature).